

Amendments to the Specification

At page 4, make the following changes to the paragraph that begins on line 9 and ends at line 16:

The HF used in etching the silicon wafers is preferably in a concentration of 0.5 to 5% by weight HF in water. The dilute HF (DHF) is preferably a solution of 0.05 to 0.25% by weight HF in water. The dilute SC1 is preferably a solution 1 part ammonium hydroxide (28% by weight) and 2 parts by weight hydrogen peroxide (30% by weight) in 50 to 200 parts water. The ozonated water in the rinse of step (B) preferably comprises less than about 10 parts per million (ppm) ozone in water. The dissolved oxygen (DO₂) is preferably controlled at less than 1 part per billion (ppb) in water. The total organic carbon (TOC) is preferably less than about 1 ppb in water. The total dissolved silica is preferably less than about 1 ppb in water.

In the paragraph that bridges from page 4, line 19 to page 5, line 10, make the following changes:

FIG. 1 is a particle signature for an in situ HF last process at 0.12 μm according to the prior art.

FIG. 2 is a particle signature for an in situ HF-last process at 0.12 μm according to the invention.

FIG. 3 is a chemical flow diagram of the chemical mixing and metering system of the present invention.

FIG. 4 is a flow chart of a comparative procedure.

FIG. 5 is a flow chart of a procedure according to the invention.

FIG. 6 is a list of the parameters used in a preferred embodiment according to the invention.

FIG. 7 a table which compares different cleaning methods and compares them to the invention method.

FIG. 8 is a control particle count diagram.

FIG. 9 is a particle count diagram of a comparative process.

~~FIG. 10 is a particle count diagram of a process according to the invention.~~

~~FIG. 6 is a particle count diagram of a process according to the invention.~~

~~FIG. 7 is a particle count diagram of a process according to the invention.~~

~~FIG. 8 is a particle count diagram of a control.~~

~~FIG. 9 is a particle count diagram of a comparative method.~~

FIG. 10 is a particle count diagram of a process according to the invention.

FIG. 11 is a particle count diagram of according to a comparative process.

FIG. 12 is a particle count diagram of a process according to the invention.

FIG. 13 is a particle count diagram of a process according to the invention

FIG. 14 is a particle count diagram after step B of the invention

FIG. 15 is a particle count of a method of the invention.

FIG. 16 is a table of data demonstrating etch and ER uniformity according to the invention.

FIG. 17 is a diagram showing defects according to the method of the invention.